

Radar Pulsed Power Transistor 30W, 3.1-3.4 GHz, 1µs Pulse, 10% Duty

M/A-COM Products Released, 10 Jul 07

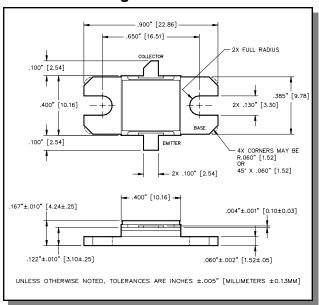
Features

- · NPN silicon microwave power transistors
- · Common base configuration
- Broadband Class C operation
- High efficiency inter-digitized geometry
- · Diffused emitter ballasting resistors
- Gold metallization system
- Internal input and output impedance matching
- Hermetic metal/ceramic package
- · RoHS compliant

Absolute Maximum Ratings at 25°C

Parameter	Symbol	Rating	Units
Collector-Emitter Voltage	V_{CES}	65	V
Emitter-Base Voltage	V_{EBO}	3.0	V
Collector Current (Peak)	Ι _C	3.6	Α
Power Dissipation @ +25°C	P _{TOT}	350	W
Storage Temperature	T _{STG}	-65 to +200	°C
Junction Temperature	T_J	200	°C

Outline Drawing



Electrical Specifications: T_C = 25 ± 5°C (Room Ambient)

Parameter	Test Conditions	Frequency	Symbol	Min	Max	Units
Collector-Emitter Breakdown Voltage	I _C = 10mA		BV _{CES}	65	-	V
Collector-Emitter Leakage Current	V _{CE} = 40V		I _{CES}	-	1.5	mA
Thermal Resistance	Vcc = 36V, Pout = 30W	F = 3.1, 3.25, 3.4 GHz	R _{TH(JC)}	-	0.5	°C/W
Input Power	Vcc = 36V, Pout = 30W	F = 3.1, 3.25, 3.4 GHz	P _{IN}	-	5.33	W
Power Gain	Vcc = 36V, Pout = 30W	F = 3.1, 3.25, 3.4 GHz	G _P	7.5	-	dB
Collector Efficiency	Vcc = 36V, Pout = 30W	F = 3.1, 3.25, 3.4 GHz	ης	35	-	%
Input Return Loss	Vcc = 36V, Pout = 30W	F = 3.1, 3.25, 3.4 GHz	RL	-	-6	dB
Load Mismatch Tolerance	Vcc = 36V, Pout = 30W	F = 3.25 GHz	VSWR-T	-	2:1	-

PRELIMINARY: Data Sheets contain information regarding a product M/A-COM has under development. Performance is based on engineering tests. Specifications are typical. Mechanical outline has been fixed. Engineering samples and/or test data may be available. Commitment to produce in volume is not guaranteed.

ADVANCED: Data Sheets contain information regarding a product M/A-COM is considering for development. Performance is based on target specifications, simulated results, and/or prototype measurements. Commitment to develop is not guaranteed.

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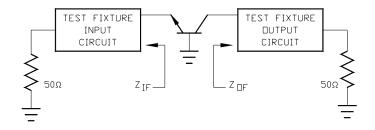
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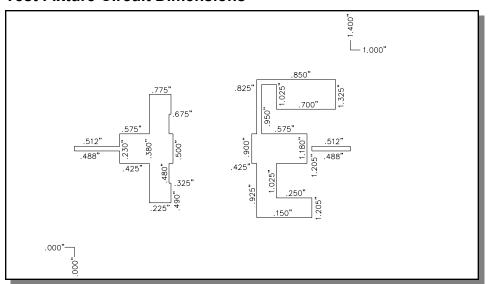
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RF Test Fixture Impedance

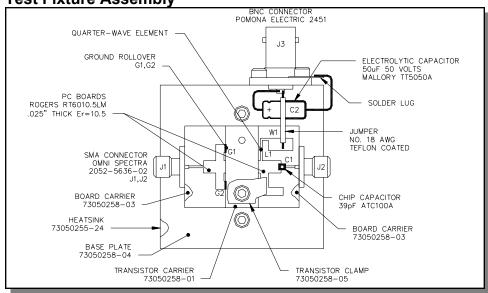
F (GHz)	Z _{IF} (Ω)	Z _{OF} (Ω)
3.10	16.0 + j5.0	19.0 + j3.0
3.25	14.5 + j2.0	15.5 - j2.0
3.40	11.5 + j0.0	10.0 - j3.5



Test Fixture Circuit Dimensions



Test Fixture Assembly



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